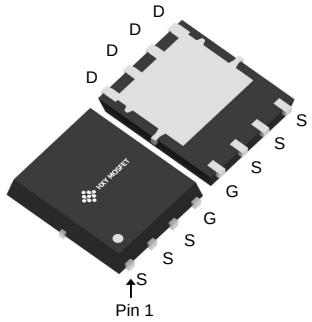
FDMS6673BZ

P-Channel Enhancement Mode MOSFET

Description

The FDMS6673BZ uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

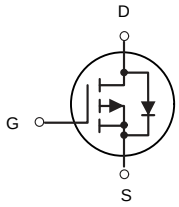


DFN5X6-8L
(POWER-56-8)

General Features

V_{DS} = -30VI $_D$ =-70A

$R_{DS(ON)}$ < 8.8mΩ V_{GS}=-10V



P-Channel MOSFET

Application

Battery protection

Load switch

Uninterruptible power supply

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
FDMS6673BZ	DFN5X6-8L(Power-56-8)	HXY MOSFET	5000

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-30	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25℃	Continuous Drain Current, V_{GS} @ 10V[1]	-70	A
I_D@T_C=75℃	Continuous Drain Current, V_{GS} @ 10V[1]	-40	A
I_{DM}	Pulsed Drain Current[2]	-175	A
EAS	Single Pulse Avalanche Energy[3]	31	mJ
P_D@T_C=25℃	Total Power Dissipation[4]	31.2	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	4	℃/W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient[1]	61	℃/W

ElectricalCharacteristics(T_J=25℃ unless otherwise noted)

Parameter		Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage		$V_{(BR)DSS}$	V_{GS} = 0V, I_D = -250μA	-30	-	-	V
Gate-body Leakage current		I_{GSS}	V_{DS} = 0V, V_{GS} = ±20V	-	-	±100	nA
Zero Gate Voltage Drain Current	T_J=25℃	I_{DSS}	V_{DS} = -24V, V_{GS} = 0V	-	-	-1	μA
	T_J=55℃			-	-	-5	
Gate-Threshold Voltage		$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = -250μA	-1.0	-1.6	-2.5	V
Drain-Source On-Resistance[2]		$R_{DS(on)}$	V_{GS} = -10V, I_D = -12A	-	6	8.8	mΩ
			V_{GS} = -4.5V, I_D = -8A	-	9	14	
Forward Transconductance		g_{fs}	V_{DS} = -5V, I_D = -20A	-	28	-	S
Input Capacitance		C_{iss}	V_{DS} = -15V, V_{GS} =0V, f =1MHz	-	4320	-	pF
Output Capacitance		C_{oss}		-	529	-	
Reverse Transfer Capacitance		C_{rss}		-	487	-	
Gate Resistance		R_g	V_{DS} = 0V, V_{GS}= 0V, f=1.0MHz	-	4.0	-	Ω
Total Gate Charge		Q_g	V_{GS} = -10V, V_{DS} = -15V, I_D= -15A	-	45	-	nC
Gate-Source Charge		Q_{gs}		-	8.5	-	
Gate-Drain Charge		Q_{gd}		-	12.8	-	
Turn-On Delay Time		$t_{d(on)}$	V_{GS} = -10V, V_{DD} = -15V, R_G = 2.5Ω, I_D= -15A	-	18.9	-	nS
Rise Time		t_r		-	15.7	-	
Turn-Off Delay Time		$t_{d(off)}$		-	64.8	-	
Fall Time		t_f		-	36.5	-	
Diode Forward Voltage[2]		V_{SD}	I_S = -1A, V_{GS} = 0V	-	-	-1	V
Continuous Source Current[1,5]		I_S	V_G=V_D=0V , Force Current	-	-	-70	A

Note :

1.The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper.

2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%

3.The EAS data shows Max. rating . The test condition is V_{DD}= -25V, V_{GS}= -10V, L= 0.1mH, I_{AS}= -25A

4.The power dissipation is limited by 150℃ junction temperature

5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Electrical And Thermal Characteristics (Curves)

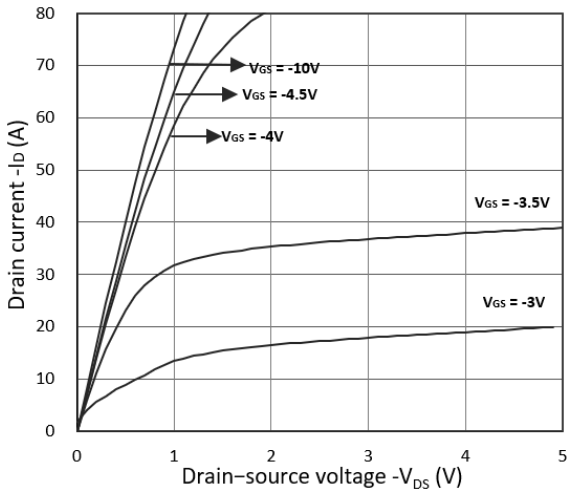


Figure 1. Output Characteristics

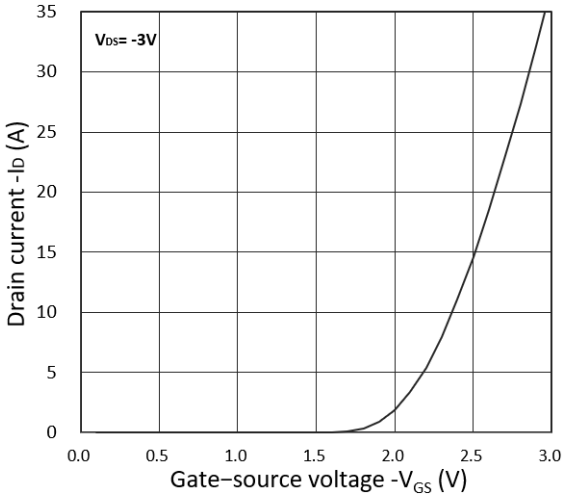


Figure 2. Transfer Characteristics

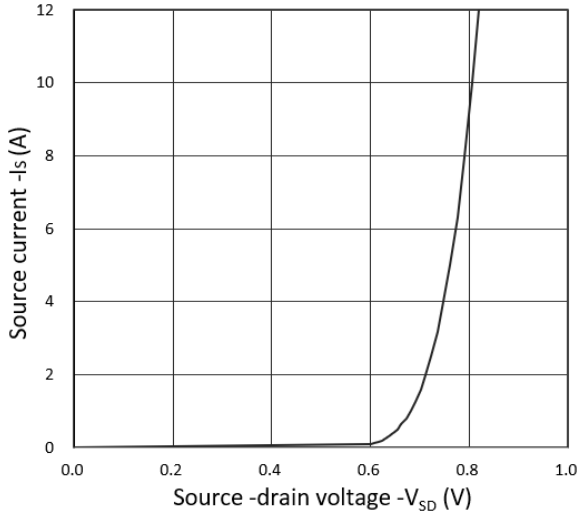


Figure 3. Forward Characteristics of Reverse

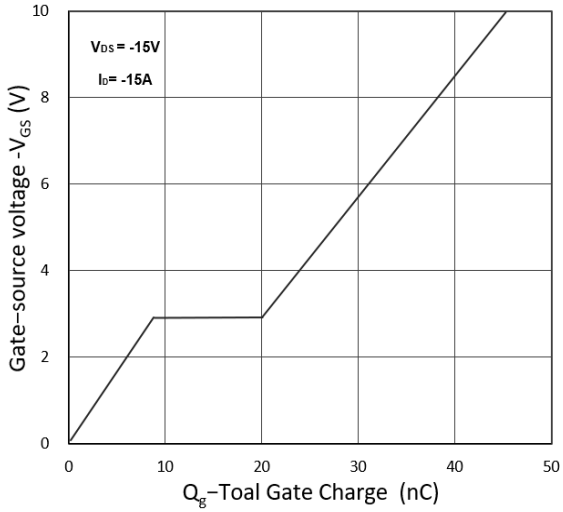


Figure 4. Gate Charge Characteristics

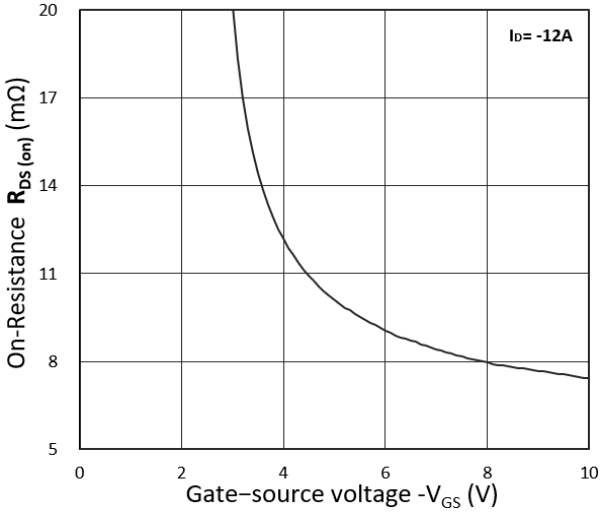


Figure 5. $R_{DS(on)}$ vs. V_{GS}

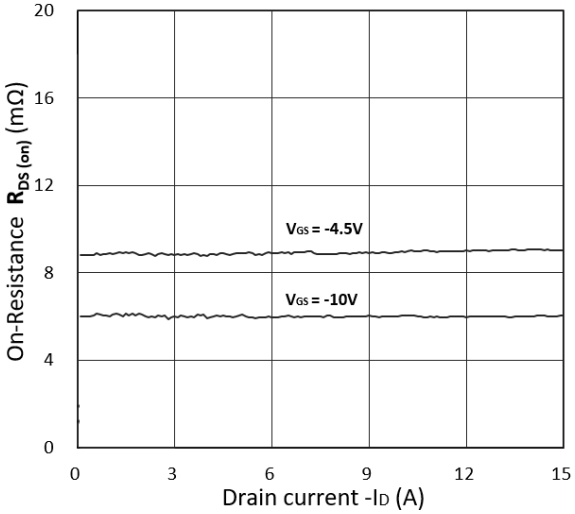


Figure 6. $R_{DS(on)}$ vs. I_D

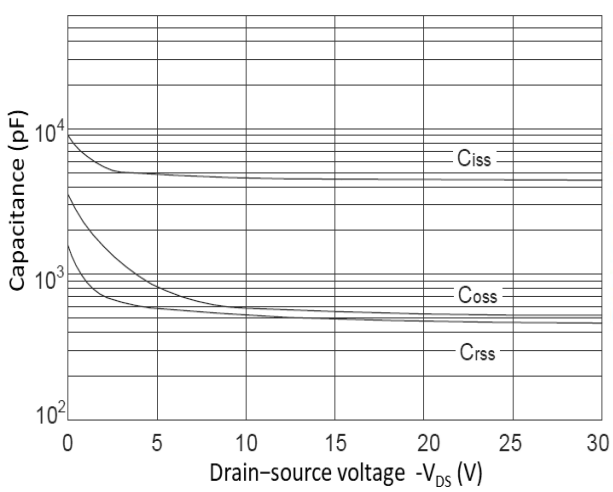


Figure 7. Capacitance Characteristics

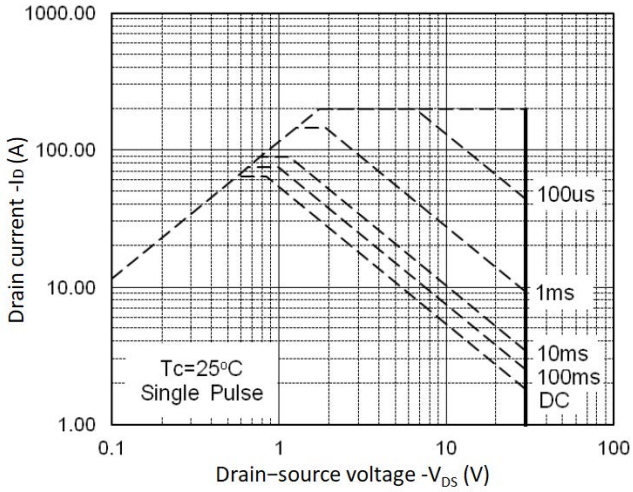


Figure 8. Safe Operating Area

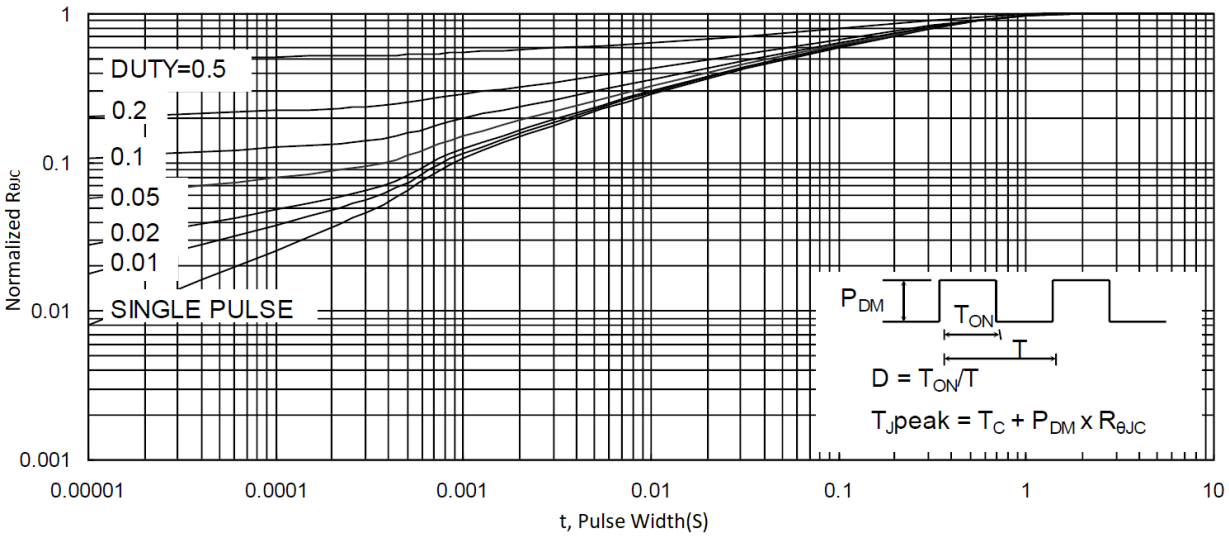


Figure 9. Normalized Maximum Transient Thermal Impedance

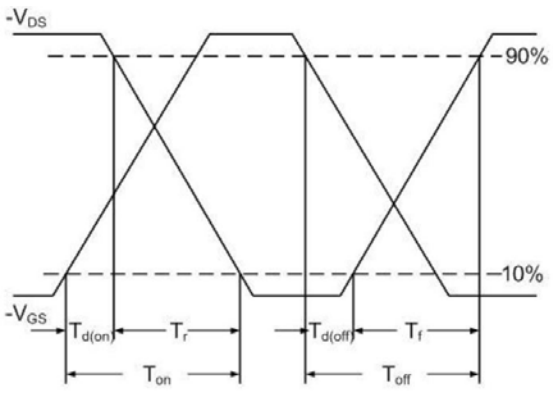


Figure 10. Switching Time Waveform

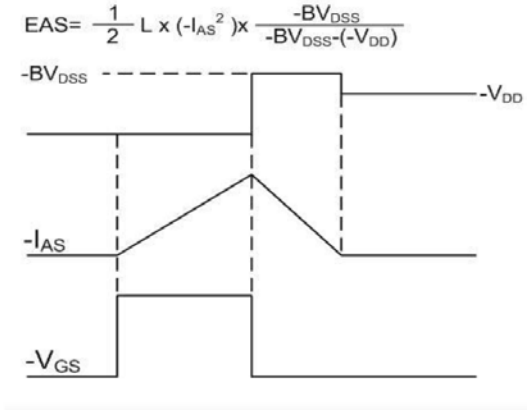
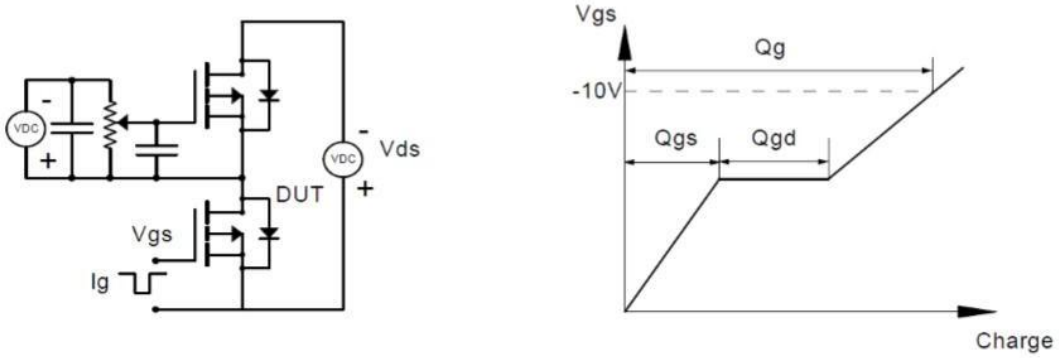


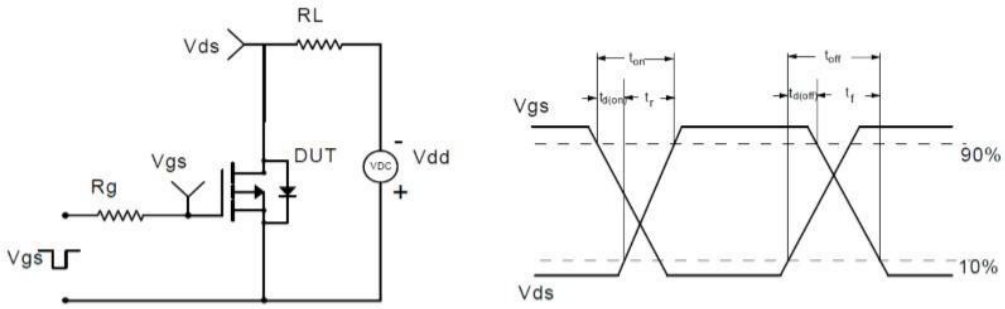
Figure 11. Unclamped Inductive Switching Waveform

Test Circuit

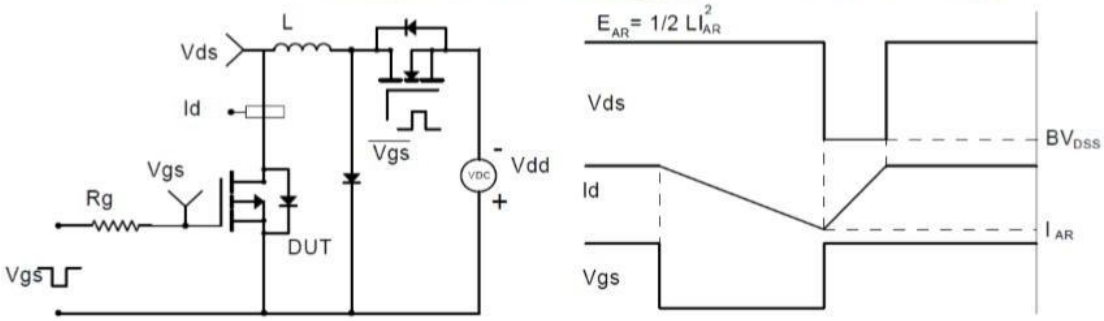
Gate Charge Test Circuit & Waveform



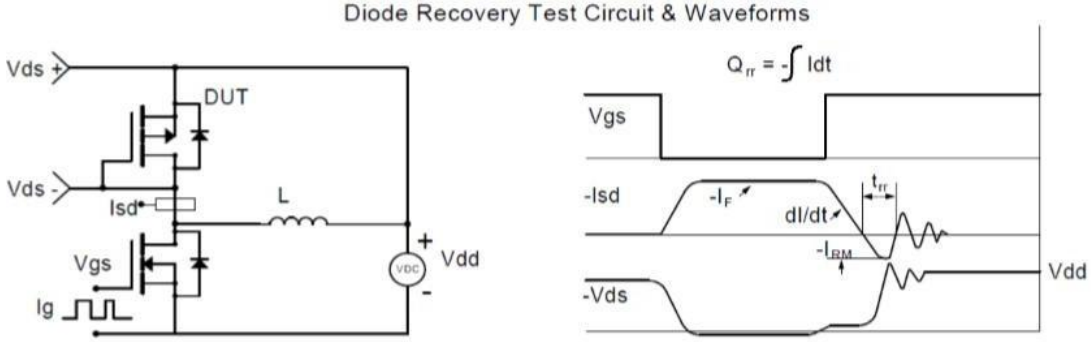
Resistive Switching Test Circuit & Waveforms



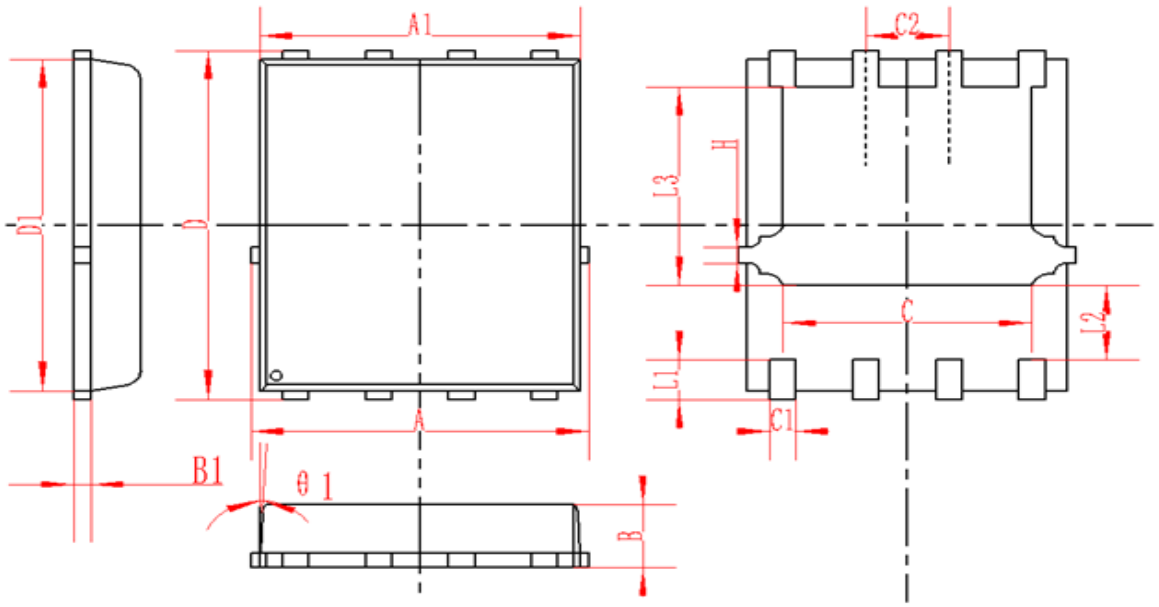
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



DFN5X6-8L(Power-56-8)Package Information



SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX
A	4.95	5	5.05	0.195	0.197	0.199
A1	4.82	4.9	4.98	0.190	0.193	0.196
D	5.98	6	6.02	0.235	0.236	0.237
D1	5.67	5.75	5.83	0.223	0.226	0.230
B	0.9	0.95	1	0.035	0.037	0.039
B1	0.254REF			0.010REF		
C	3.95	4	4.05	0.156	0.157	0.159
C1	0.35	0.4	0.45	0.014	0.016	0.018
C2	1.27TYP			0.5TYP		
θ1	8°	10°	12°	8°	10°	12°
L1	0.63	0.64	0.65	0.025	0.025	0.026
L2	1.2	1.3	1.4	0.047	0.051	0.055
L3	3.415	3.42	3.425	0.134	0.135	0.135
H	0.24	0.25	0.26	0.009	0.010	0.010

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HT7150 P6SMB200A SS10100 HXY8205ES SS5150B TPSMB100CA-VR HMCP602-I/SN PESD5V0S1BB
BZT52C13 HC4D20120A P6SMB36CA HAD8542ARZ P6SMB33CA SS510C TPSMB28A-VR US2M